

BSR50

NPN Darlington Transistor

- This device designed for applications requiring extremely high gain at collector currents to 0.5A.
- Sourced from Process 06.



1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_A =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V_{CEO}	Collector-Emitter Voltage	45	V	
V_{CBO}	Collector-Base Voltage	60	V	
V_{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current	1.5	Α	
T _J , T _{STG}	Storage Temperature	-55 ~ 150	°C	

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{\textbf{A}} = 25 ^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	45			V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_B = 0$	60			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 45V, I_{E} = 0$			50	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4.0V, I_{C} = 0$			50	nA
h _{FE}	DC Current Gain	$V_{CE} = 10V, I_{C} = 150mA$ $V_{CE} = 10V, I_{C} = 0.5A$	1,000 2,000			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{A}, I_B = 4.0 \text{mA}$			1.3 1.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{mA}, I_B = 4.0 \text{mA}$			0.9 2.2	V

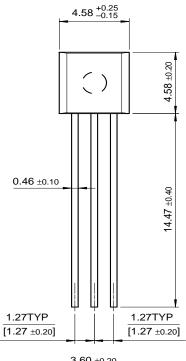
Thermal Characteristics $T_A=25$ °C unless otherwise noted

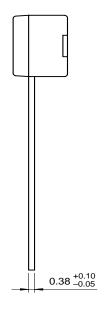
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation 625		mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient 200		°C/W

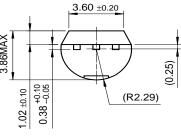
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Package Dimensions

TO-92







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